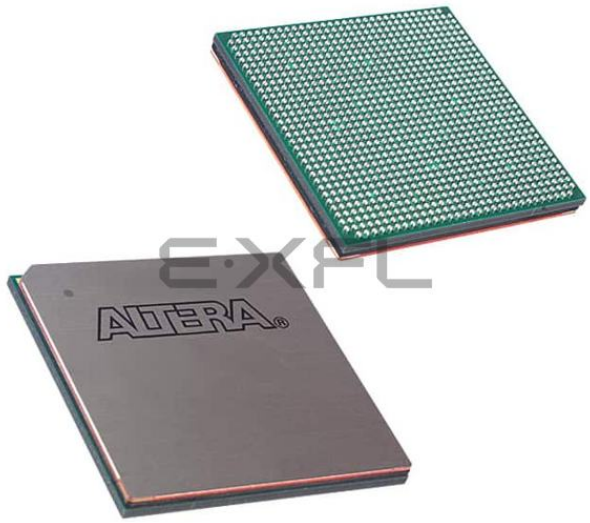

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	5184
Number of Logic Elements/Cells	51840
Total RAM Bits	442368
Number of I/O	808
Number of Gates	2392000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1020-BBGA
Supplier Device Package	1020-FBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k1500efc33-2

Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations
- Altera MegaCore® functions and Altera Megafunction Partners Program (AMPP℠) megafunctions
- NativeLink™ integration with popular synthesis, simulation, and timing analysis tools
- Quartus II SignalTap® embedded logic analyzer simplifies in-system design evaluation by giving access to internal nodes during device operation
- Supports popular revision-control software packages including PVCS, Revision Control System (RCS), and Source Code Control System (SCCS)

Table 4. APEX 20K QFP, BGA & PGA Package Options & I/O Count *Notes (1), (2)*

Device	144-Pin TQFP	208-Pin PQFP RQFP	240-Pin PQFP RQFP	356-Pin BGA	652-Pin BGA	655-Pin PGA
EP20K30E	92	125				
EP20K60E	92	148	151	196		
EP20K100	101	159	189	252		
EP20K100E	92	151	183	246		
EP20K160E	88	143	175	271		
EP20K200		144	174	277		
EP20K200E		136	168	271	376	
EP20K300E			152		408	
EP20K400					502	502
EP20K400E					488	
EP20K600E					488	
EP20K1000E					488	
EP20K1500E					488	

General Description

APEX™ 20K devices are the first PLDs designed with the MultiCore architecture, which combines the strengths of LUT-based and product-term-based devices with an enhanced memory structure. LUT-based logic provides optimized performance and efficiency for data-path, register-intensive, mathematical, or digital signal processing (DSP) designs. Product-term-based logic is optimized for complex combinatorial paths, such as complex state machines. LUT- and product-term-based logic combined with memory functions and a wide variety of MegaCore and AMPP functions make the APEX 20K device architecture uniquely suited for system-on-a-programmable-chip designs. Applications historically requiring a combination of LUT-, product-term-, and memory-based devices can now be integrated into one APEX 20K device.

APEX 20KE devices are a superset of APEX 20K devices and include additional features such as advanced I/O standard support, CAM, additional global clocks, and enhanced ClockLock clock circuitry. In addition, APEX 20KE devices extend the APEX 20K family to 1.5 million gates. APEX 20KE devices are denoted with an "E" suffix in the device name (e.g., the EP20K1000E device is an APEX 20KE device). Table 8 compares the features included in APEX 20K and APEX 20KE devices.

Table 8. Comparison of APEX 20K & APEX 20KE Features

Feature	APEX 20K Devices	APEX 20KE Devices
MultiCore system integration	Full support	Full support
SignalTap logic analysis	Full support	Full support
32/64-Bit, 33-MHz PCI	Full compliance in -1, -2 speed grades	Full compliance in -1, -2 speed grades
32/64-Bit, 66-MHz PCI	-	Full compliance in -1 speed grade
MultiVolt I/O	2.5-V or 3.3-V V_{CCIO} V_{CCIO} selected for device Certain devices are 5.0-V tolerant	1.8-V, 2.5-V, or 3.3-V V_{CCIO} V_{CCIO} selected block-by-block 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction 2× and 4× clock multiplication	Clock delay reduction $m/(n \times v)$ or $m/(n \times k)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift LVDS support Up to four PLLs ClockShift, clock phase adjustment
Dedicated clock and input pins	Six	Eight
I/O standard support	2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI Low-voltage complementary metal-oxide semiconductor (LVCMOS) Low-voltage transistor-to-transistor logic (LVTTL)	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 2.5-V I/O 3.3-V PCI and PCI-X 3.3-V Advanced Graphics Port (AGP) Center tap terminated (CTT) GTL+ LVCMOS LVTTL True-LVDS and LVPECL data pins (in EP20K300E and larger devices) LVDS and LVPECL signaling (in all BGA and FineLine BGA devices) LVDS and LVPECL data pins up to 156 Mbps (in -1 speed grade devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	Dual-port RAM FIFO RAM ROM	CAM Dual-port RAM FIFO RAM ROM

Functional Description

APEX 20K devices incorporate LUT-based logic, product-term-based logic, and memory into one device. Signal interconnections within APEX 20K devices (as well as to and from device pins) are provided by the FastTrack® Interconnect—a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a register that can be used as either an input or output register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. IOEs provide a variety of features, such as 3.3-V, 64-bit, 66-MHz PCI compliance; JTAG BST support; slew-rate control; and tri-state buffers. APEX 20KE devices offer enhanced I/O support, including support for 1.8-V I/O, 2.5-V I/O, LVCMOS, LVTTL, LVPECL, 3.3-V PCI, PCI-X, LVDS, GTL+, SSTL-2, SSTL-3, HSTL, CTT, and 3.3-V AGP I/O standards.

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs ensures that the APEX 20K device can implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. The abundance of ESBs ensures that designers can create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20K device.

Figure 1. APEX 20K Device Block Diagram

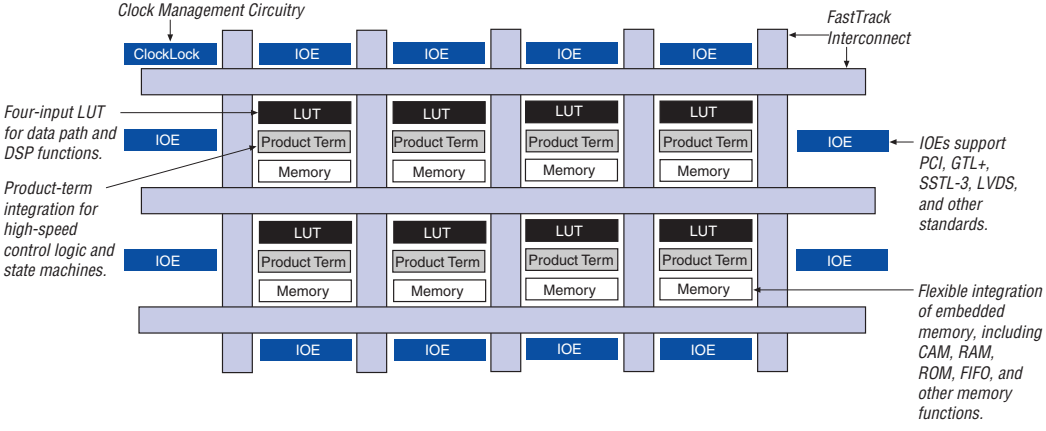


Figure 6. APEX 20K Carry Chain

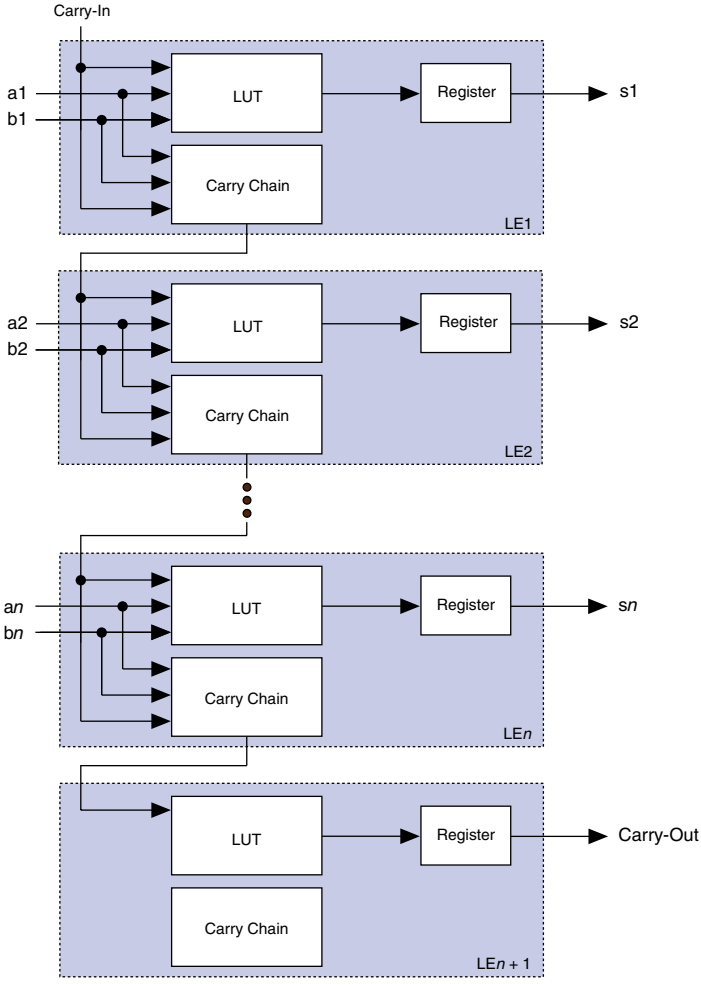
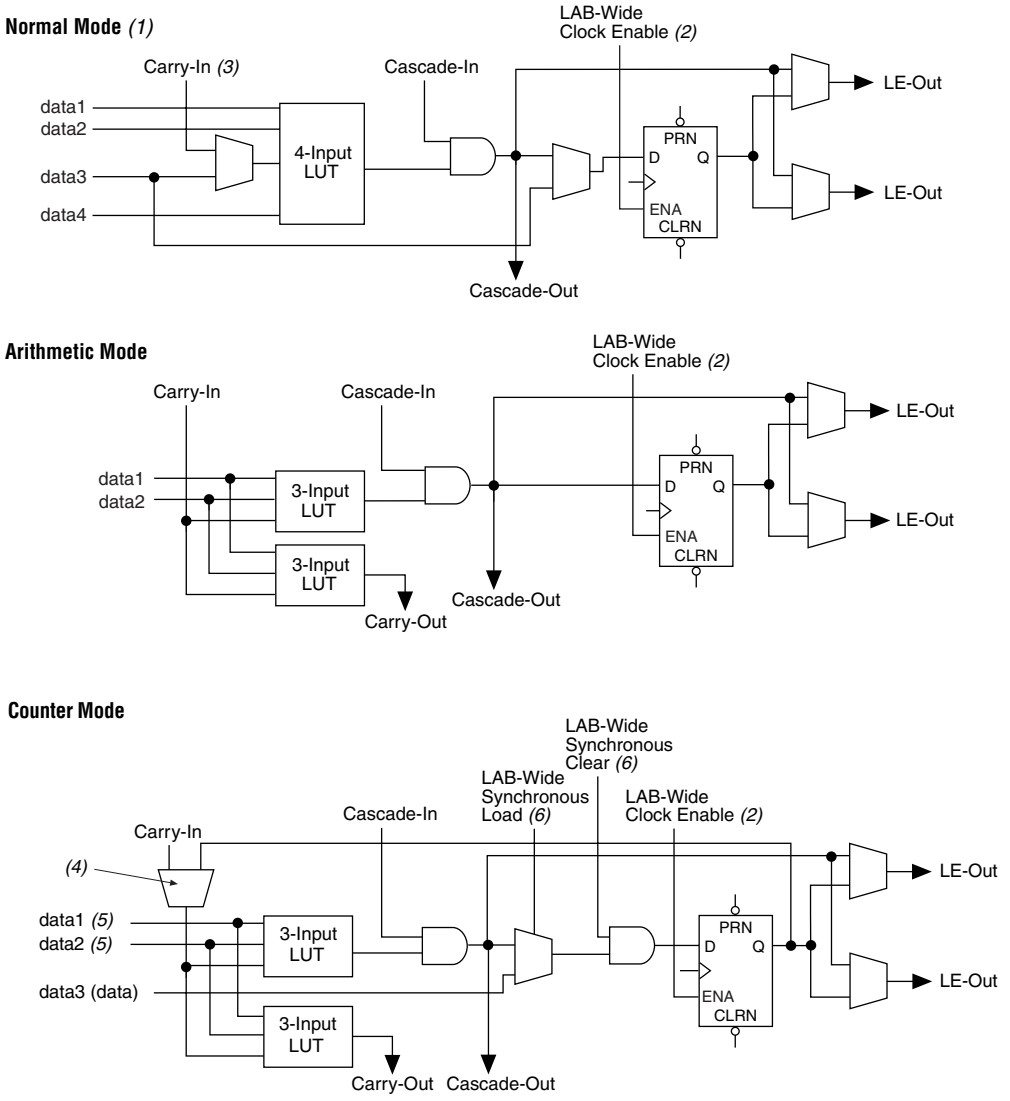


Figure 8. APEX 20K LE Operating Modes



Notes to Figure 8:

(1) LEs in normal mode support register packing.
(2) There are two LAB-wide clock enables per LAB.
(3) When using the carry-in in normal mode, the packed register feature is unavailable.
(4) A register feedback multiplexer is available on LE1 of each LAB.
(5) The DATA1 and DATA2 input signals can supply counter enable, up or down control, or register feedback signals for LEs other than the second LE in an LAB.
(6) The LAB-wide synchronous clear and LAB wide synchronous load affect all registers in an LAB.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

APEX 20KE devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KE IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KE IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II software compiler can set these delays automatically to minimize setup time while providing a zero hold time.

Table 11 describes the APEX 20KE programmable delays and their logic options in the Quartus II software.

Table 11. APEX 20KE Programmable Delay Chains

Programmable Delays	Quartus II Logic Option
Input Pin to Core Delay	Decrease input delay to internal cells
Input Pin to Input Register Delay	Decrease input delay to input registers
Core to Output Register Delay	Decrease input delay to output register
Output Register t_{CO} Delay	Increase delay to output pin
Clock Enable Delay	Increase clock enable delay

The register in the APEX 20KE IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. Figure 26 shows how fast bidirectional I/O pins are implemented in APEX 20KE devices. This feature is useful for cases where the APEX 20KE device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Table 15. APEX 20K ClockLock & ClockBoost Parameters for -1 Speed-Grade Devices (Part 2 of 2)

Symbol	Parameter	Min	Max	Unit
t_{SKEW}	Skew delay between related ClockLock/ClockBoost-generated clocks		500	ps
t_{JITTER}	Jitter on ClockLock/ClockBoost-generated clock *(5)*		200	ps
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)		50	ps

Notes to Table 15:

(1) The PLL input frequency range for the EP20K100-1X device for 1x multiplication is 25 MHz to 175 MHz.
(2) All input clock specifications must be met. The PLL may not lock onto an incoming clock if the clock specifications are not met, creating an erroneous clock within the device.
(3) During device configuration, the ClockLock and ClockBoost circuitry is configured first. If the incoming clock is supplied during configuration, the ClockLock and ClockBoost circuitry locks during configuration, because the lock time is less than the configuration time.
(4) The jitter specification is measured under long-term observation.
(5) If the input clock stability is 100 ps, t_{JITTER} is 250 ps.

Table 16 summarizes the APEX 20K ClockLock and ClockBoost parameters for -2 speed grade devices.

Table 16. APEX 20K ClockLock & ClockBoost Parameters for -2 Speed Grade Devices

Symbol	Parameter	Min	Max	Unit
f_{OUT}	Output frequency	25	170	MHz
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)	25	170	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16	80	MHz
f_{CLK4}	Input clock frequency (ClockBoost clock multiplication factor equals 4)	10	34	MHz
$t_{OUTDUTY}$	Duty cycle for ClockLock/ClockBoost-generated clock	40	60	%
f_{CLKDEV}	Input deviation from user specification in the Quartus II software (ClockBoost clock multiplication factor equals one) *(1)*		25,000 *(2)*	PPM
t_R	Input rise time		5	ns
t_F	Input fall time		5	ns
t_{LOCK}	Time required for ClockLock/ ClockBoost to acquire lock *(3)*		10	µs
t_{SKEW}	Skew delay between related ClockLock/ ClockBoost-generated clock	500	500	ps
t_{JITTER}	Jitter on ClockLock/ ClockBoost-generated clock *(4)*		200	ps
$t_{INCLKSTB}$	Input clock stability (measured between adjacent clocks)		50	ps

Table 26. APEX 20K 5.0-V Tolerant Device Capacitance *Notes (2), (14)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Tables 23 through 26:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) All APEX 20K devices are 5.0-V tolerant.
(3) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V or overshoot to 5.75 V for input currents less than 100 mA and periods shorter than 20 ns.
(4) Numbers in parentheses are for industrial-temperature-range devices.
(5) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(6) All pins, including dedicated inputs, clock I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
(7) Typical values are for T_A = 25° C, V_{CCINT} = 2.5 V, and V_{CCIO} = 2.5 or 3.3 V.
(8) These values are specified in the APEX 20K device recommended operating conditions, shown in Table 26 on page 62.
(9) The APEX 20K input buffers are compatible with 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant when V_{CCIO} and V_{CCINT} meet the relationship shown in Figure 33 on page 68.
(10) The I_{OH} parameter refers to high-level TTL, PCI or CMOS output current.
(11) The I_{OL} parameter refers to low-level TTL, PCI, or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(12) This value is specified for normal device operation. The value may vary during power-up.
(13) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(14) Capacitance is sample-tested only.

Tables 27 through 30 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V APEX 20KE devices.

Table 27. APEX 20KE Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, RQFP, TQFP, and BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 28. APEX 20KE Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	*(5)*, *(6)*	–0.5	4.0	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

All specifications are always representative of worst-case supply voltage and junction temperature conditions. All output-pin-timing specifications are reported for maximum driver strength.

Figure 36 shows the f_{MAX} timing model for APEX 20K devices.

Figure 36. APEX 20K f_{MAX} Timing Model

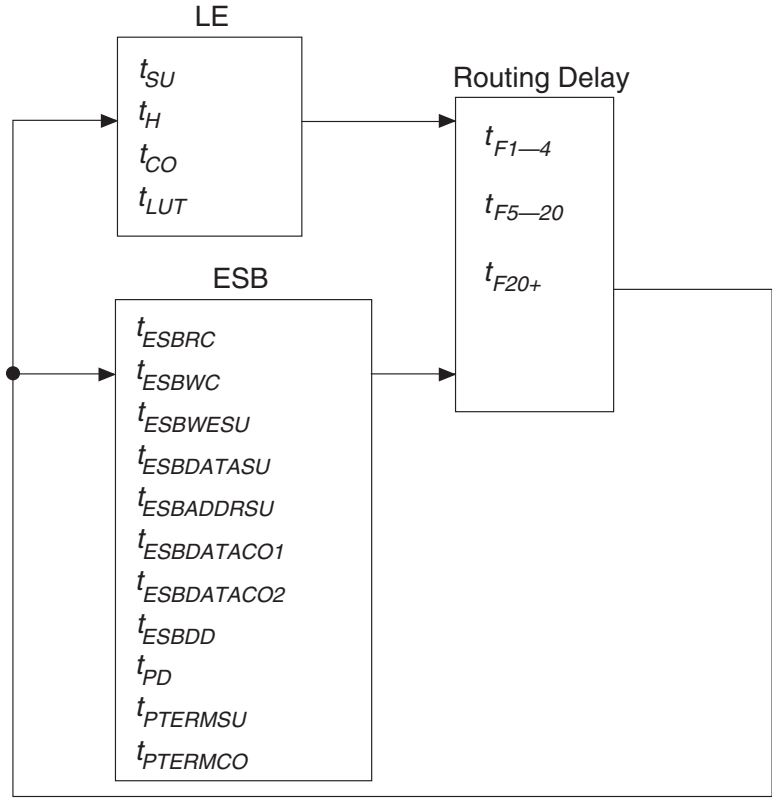


Figure 37 shows the f_{MAX} timing model for APEX 20KE devices. These parameters can be used to estimate f_{MAX} for multiple levels of logic. Quartus II software timing analysis should be used for more accurate timing information.

Table 39. APEX 20KE External Bidirectional Timing Parameters Note (1)		
Symbol	**Parameter**	**Conditions**
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at LAB adjacent Input Register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at LAB adjacent Input Register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE output register	C1 = 10 pF
$t_{XZBIDIR}$	Synchronous Output Enable Register to output buffer disable delay	C1 = 10 pF
$t_{ZXBIDIR}$	Synchronous Output Enable Register output buffer enable delay	C1 = 10 pF
$t_{INSUBIDIRPLL}$	Setup time for bidirectional pins with PLL clock at LAB adjacent Input Register	
$t_{INHBIDIRPLL}$	Hold time for bidirectional pins with PLL clock at LAB adjacent Input Register	
$t_{OUTCOBIDIRPLL}$	Clock-to-output delay for bidirectional pins with PLL clock at IOE output register	C1 = 10 pF
$t_{XZBIDIRPLL}$	Synchronous Output Enable Register to output buffer disable delay with PLL	C1 = 10 pF
$t_{ZXBIDIRPLL}$	Synchronous Output Enable Register output buffer enable delay with PLL	C1 = 10 pF

Note to Tables 38 and 39:
(1) These timing parameters are sample-tested only.

Tables 40 through 42 show the f_{MAX} timing parameters for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Table 40. EP20K100 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.6		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.5		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Notes to Tables 43 through 48:
(1) This parameter is measured without using ClockLock or ClockBoost circuits.
(2) This parameter is measured using ClockLock or ClockBoost circuits.

Tables 49 through 54 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K30E APEX 20KE devices.

Table 49. EP20K30E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.02		0.02		ns
t_{H}	0.11		0.16		0.23		ns
t_{CO}		0.32		0.45		0.67	ns
t_{LUT}		0.85		1.20		1.77	ns

Table 56. EP20K60E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.83		2.57		3.79	ns
t_{ESBSRC}		2.46		3.26		4.61	ns
t_{ESBAWC}		3.50		4.90		7.23	ns
t_{ESBSWC}		3.77		4.90		6.79	ns
$t_{ESBWASU}$	1.59		2.23		3.29		ns
t_{ESBWAH}	0.00		0.00		0.00		ns
$t_{ESBWDSU}$	1.75		2.46		3.62		ns
t_{ESBWDH}	0.00		0.00		0.00		ns
$t_{ESBRASU}$	1.76		2.47		3.64		ns
t_{ESBRAH}	0.00		0.00		0.00		ns
$t_{ESBWESU}$	1.68		2.49		3.87		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.08		0.43		1.04		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.29		0.72		1.46		ns
$t_{ESBRADDRSU}$	0.36		0.81		1.58		ns
$t_{ESBDATACO1}$		1.06		1.24		1.55	ns
$t_{ESBDATACO2}$		2.39		3.35		4.94	ns
t_{ESBDD}		3.50		4.90		7.23	ns
t_{PD}		1.72		2.41		3.56	ns
$t_{PTERMSU}$	0.99		1.56		2.55		ns
$t_{PTERMCO}$		1.07		1.26		1.08	ns

Tables 85 through 90 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K400E APEX 20KE devices.

Table 85. EP20K400E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.23		0.23		0.23		ns
t_{H}	0.23		0.23		0.23		ns
t_{CO}		0.25		0.29		0.32	ns
t_{LUT}		0.70		0.83		1.01	ns

Table 90. EP20K400E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.93		3.23		3.44		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{XZBIDIR}$		5.95		6.77		7.12	ns
$t_{ZXBIDIR}$		5.95		6.77		7.12	ns
$t_{INSUBIDIRPLL}$	4.31		4.76		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.45	-	-	ns
$t_{XZBIDIRPLL}$		2.94		3.43		-	ns
$t_{ZXBIDIRPLL}$		2.94		3.43		-	ns

Tables 91 through 96 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K600E APEX 20KE devices.

Table 91. EP20K600E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.16		0.17		ns
t_{H}	0.29		0.33		0.37		ns
t_{CO}		0.65		0.38		0.49	ns
t_{LUT}		0.70		1.00		1.30	ns

Table 98. EP20K1000E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.78		2.02		1.95	ns
t_{ESBSRC}		2.52		2.91		3.14	ns
t_{ESBAWC}		3.52		4.11		4.40	ns
t_{ESBSWC}		3.23		3.84		4.16	ns
$t_{ESBWASU}$	0.62		0.67		0.61		ns
t_{ESBWAH}	0.41		0.55		0.55		ns
$t_{ESBWDSU}$	0.77		0.79		0.81		ns
t_{ESBWDH}	0.41		0.55		0.55		ns
$t_{ESBRASU}$	1.74		1.92		1.85		ns
t_{ESBRAH}	0.00		0.01		0.23		ns
$t_{ESBWESU}$	2.07		2.28		2.41		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	0.25		0.27		0.29		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.04		0.11		ns
$t_{ESBRADDRSU}$	0.14		0.11		0.16		ns
$t_{ESBDATACO1}$		1.29		1.50		1.63	ns
$t_{ESBDATACO2}$		2.55		2.99		3.22	ns
t_{ESBDD}		3.12		3.57		3.85	ns
t_{PD}		1.84		2.13		2.32	ns
$t_{PTERMSU}$	1.08		1.19		1.32		ns
$t_{PTERMCO}$		1.31		1.53		1.66	ns

Table 110. Selectable I/O Standard Output Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min
LVCMOS		0.00		0.00		0.00	ns
LVTTL		0.00		0.00		0.00	ns
2.5 V		0.00		0.09		0.10	ns
1.8 V		2.49		2.98		3.03	ns
PCI		–0.03		0.17		0.16	ns
GTL+		0.75		0.75		0.76	ns
SSTL-3 Class I		1.39		1.51		1.50	ns
SSTL-3 Class II		1.11		1.23		1.23	ns
SSTL-2 Class I		1.35		1.48		1.47	ns
SSTL-2 Class II		1.00		1.12		1.12	ns
LVDS		–0.48		–0.48		–0.48	ns
CTT		0.00		0.00		0.00	ns
AGP		0.00		0.00		0.00	ns

Power Consumption

To estimate device power consumption, use the interactive power calculator on the Altera web site at **http://www.altera.com**.

Configuration & Operation

The APEX 20K architecture supports several configuration schemes. This section summarizes the device operating modes and available device configuration schemes.

Operating Modes

The APEX architecture uses SRAM configuration elements that require configuration data to be loaded each time the circuit powers up. The process of physically loading the SRAM data into the device is called configuration. During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

Before and during device configuration, all I/O pins are pulled to V_{CCIO} by a built-in weak pull-up resistor.